August 1998

54FCT573 Octal D-Type Latch with TRI-STATE Outputs

National Semiconductor

### 54FCT573 Octal D-Type Latch with TRI-STATE<sup>®</sup> Outputs

#### **General Description**

The 'FCT573 is an octal latch with buffered common Latch Enable (LE) and buffered common Output Enable  $(\overline{\text{OE}})$  inputs.

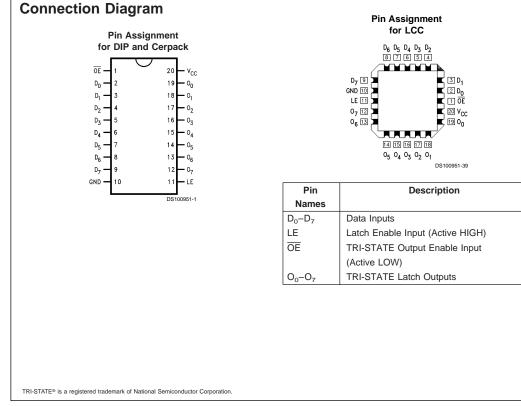
This device is functionally identical to the 'FCT373 but has different pinouts.

#### Features

- Inputs and outputs on opposite sides of package allow easy interface with microprocessors
- Useful as input or output port for microprocessors
- TTL input and output level compatible
- CMOS power consumption
- Functionally identical to 'FCT373
- TRI-STATE outputs for bus interfacing
- Output sink capability of 32 mA, source capability of 12 mA
- Standard Microcircuit Drawing (SMD) 5962-8863901

#### **Ordering Code**

Military	Package	Package Description
	Number	
54FCT573DMQB	J20A	20-Lead Ceramic Dual-In-Line
54FCT573FMQB	W20A	20-Lead Cerpack
54FCT573LMQB	E20A	20-Lead Ceramic Leadless Chip Carrier, Type C



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# 54FCT573

#### **Functional Description**

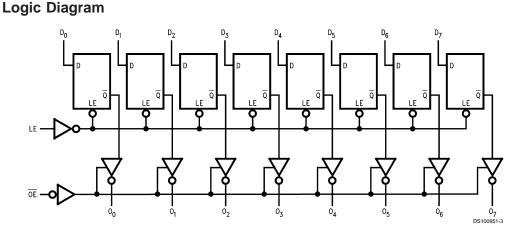
The 'FCT573 contains eight D-type latches with TRI-STATE output buffers. When the Latch Enable (LE) input is HIGH, data on the  $D_n$  inputs enters the latches. In this condition the latches are transparent, i.e., a latch output will change state each time its D input changes. When LE is LOW the latches store the information that was present on the D inputs a setup time preceding the HIGH-to-LOW transition of LE. The TRI-STATE buffers are controlled by the Output Enable ( $\overline{OE}$ ) input. When  $\overline{OE}$  is LOW, the buffers are in the bi-state mode. When  $\overline{OE}$  is HIGH the buffers are in the high impedance mode but this does not interfere with entering new data into the latches.

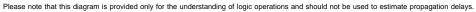
Function Table							
Inputs Outputs							
OE	LE	D	0				
L	Н	Н	Н				
L	Н	L	L				
L	L	Х	Oo				
Н	Х	Х	Z				

H = HIGH Voltage Level

L = LOW Voltage Level

 $\begin{array}{l} X = Immaterial \\ O_0 = Value \mbox{ stored from previous clock cycle} \end{array}$ 





#### Absolute Maximum Ratings (Note 1)

If Military/Aerospace specified devices are required, please contact the National Semiconductor Sales Office/ Distributors for availability and specifications.

Storage Temperature	–65°C to +150°C
Ambient Temperature under Bias	–55°C to +125°C
Junction Temperature under Bias	
Ceramic	–55°C to +175°C
V <sub>CC</sub> Pin Potential to	
Ground Pin	-0.5V to +7.0V
Input Voltage (Note 2)	-0.5V to +7.0V
Input Current (Note 2)	-30 mA to +5.0 mA
Voltage Applied to Any Output	
in the Disabled or	
Power-Off State	-0.5V to +5.5V
in the HIGH State	–0.5V to V <sub>CC</sub>
Current Applied to Output	

in LOW State (Max) DC Latchup Source Current Twice the rated  $\rm I_{OL}$  (mA)  $-500~\rm mA$ 

54FCT573

# Recommended Operating Conditions

Free Air Ambient Temperature					
Military	–55°C to +125°C				
Supply Voltage					
Military	+4.5V to +5.5V				
Minimum Input Edge Rate	$(\Delta V / \Delta t)$				
Data Input	50 mV/ns				
Enable Input	20 mV/ns				
<b>Note 1:</b> Absolute maximum ratings are values beyond which the device may be damaged or have its useful life impaired. Functional operation under these conditions is not implied.					
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Note 2: Either voltage limit or current limit is sufficient to protect inputs.

#### **DC Electrical Characteristics**

Symbol Pai	Parameter		FCT573		Units	V <sub>cc</sub>	Conditions		
				Min Typ Max					
VIH	Input HIGH Voltage		2.0			V		Recognized HIGH Signal	
VIL	Input LOW Voltage				0.8	V		Recognized LOW Signal	
V <sub>CD</sub>	Input Clamp Diode Voltage				-1.2	V	Min	$I_{IN} = -18 \text{ mA}$	
V <sub>OH</sub>	Output HIGH Voltage	54FCT	4.3			V	Min	I <sub>OH</sub> = -300 μA	
		54FCT	2.4					$I_{OH} = -12 \text{ mA}$	
V <sub>OL</sub>	Output LOW Voltage	54FCT			0.2	V	Min	I <sub>OL</sub> = 300 μA	
		54FCT			0.5			I <sub>OL</sub> = 32 mA	
IIH	Input HIGH Current				5	μA	Max	$V_{IN} = V_{CC}$	
IIL .	Input LOW Current				-5	μA	Max	$V_{IN} = 0.0V$	
I <sub>OZH</sub>	Output Leakage Current				50	μA	0 – 5.5V	$V_{OUT} = 2.7V; \overline{OE} = 2.0V$	
I <sub>OZL</sub>	Output Leakage Current				-50	μA	0 – 5.5V	$V_{OUT} = 0.5V; \overline{OE} = 2.0V$	
los	Output Short-Circuit Current				-60	mA	Max	$V_{OUT} = 0.0V$	
Iccq	Quiescent Power Supply Current				1.5	mA	Max	$V_{IN}$ < 0.2V or $V_{IN}$ 5.3V, $V_{CC}$ = 5.5V	
$\Delta I_{CC}$	Quiescent Power Supply Current				2.0	mA	Max	$V_1 = 3.4V, V_{CC} = 5.5V$	
I <sub>CCD</sub>	Dynamic I <sub>CC</sub>				0.4	mA/ MHz	Max	$ \begin{array}{ c c c c c c c c c c c c c c c c c c c$	
I <sub>cc</sub>	Total Power Supply Current				6.0	mA	Max	$\begin{array}{l} \mbox{Outputs Open, } f_{CP} = 10 \mbox{ MHz,} \\ V_{CC} = 5.5V, \mbox{ V}_{IN} \mbox{ 5.3V or } V_{IN} \mbox{ <} \\ 0.2V, \mbox{ One Bit Toggling, } 50\% \\ \mbox{Duty Cycle, } \overline{OE} = \mbox{ GND, } LE = \\ V_{CC} \end{array}$	

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Symbol	Parameter	541	FCT	Units	Fig. No.
		T <sub>A</sub> = -55°C	C to +125°C		
		$V_{\rm CC} = 4.8$	5V to 5.5V		
		C <sub>L</sub> =	50 pF		
		Min	Max		
t <sub>PLH</sub>	Propagation Delay	1.0	8.5	ns	Figure 4
t <sub>PHL</sub>	D <sub>n</sub> to O <sub>n</sub>	1.0	8.5		
t <sub>PLH</sub>	Propagation Delay	1.0	15.0	ns	Figure 4
t <sub>PHL</sub>	LE to O <sub>n</sub>	1.0	15.0		
t <sub>PZH</sub>	Output Enable Time	1.0	13.5	ns	Figure 6
t <sub>PZL</sub>		1.0	13.5		
t <sub>PHZ</sub>	Output Disable Time	1.0	10.0	ns	Figure 6
t <sub>PLZ</sub>	Time	1.0	10.0		

# **AC Operating Requirements**

Symbol	bol Parameter 54FCT		Units	Fig.	
		$T_{A} = -55^{\circ}$	C to +125°C		No.
		$V_{\rm CC} = 4.$	5V to 5.5V		
		C <sub>L</sub> =	$C_{L} = 50 \text{ pF}$		
		Min	Max	· ۲	
t <sub>s</sub> (H)	Set Time, HIGH	2.0		ns	Figure 7
t <sub>s</sub> (L)	or LOW D <sub>n</sub> to LE	2.0			
t <sub>h</sub> (H)	Hold Time, HIGH	1.5		ns	Figure 7
t <sub>h</sub> (L)	or LOW D <sub>n</sub> to LE	1.5			
t <sub>w</sub> (H)	Pulse Width,	6.0		ns	Figure 5
	LE HIGH				

# Capacitance

Symbol	Parameter	Max	Units	Conditions
				(T <sub>A</sub> = 25°C)
C <sub>IN</sub>	Input Capacitance	10	pF	$V_{\rm CC} = 0V$
C <sub>OUT</sub> (Note 3)	Output Capacitance	12	pF	$V_{\rm CC} = 5.0 V$

Note 3:  $C_{OUT}$  is measured at frequency f = 1 MHz per MIL-STD-883B, Method 3012.

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